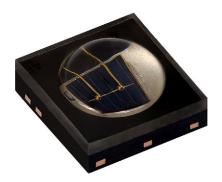
### Vishay Semiconductors

## High Power Infrared Emitting Diode, 940 nm, Surface Emitter Technology



www.vishay.com

### LINKS TO ADDITIONAL RESOURCES



### DESCRIPTION

As part of the <u>Astral</u> portfolio, the VSMA1094601X02 is an infrared, 940 nm emitting diode. It features a double stack emitter chip for highest radiant power while minimizing the red glow effect. The 42 mil chip size allows 1.5 A DC operation and supports pulsed currents up to 5.0 A.

### FEATURES

### Package type: surface-mount

- Package form: high power SMD with lens
- Dimensions (L x W x H in mm): 3.4 x 3.4 x 1.8
- Peak wavelength:  $\lambda_p = 950 \text{ nm}$
- AEC-Q102 qualified
- Angle of half intensity:  $\varphi = \pm 60^{\circ}$
- Designed for high drive currents: up to 1.5 A (DC) and up to 5 A (pulsed)
- Low thermal resistance: R<sub>thJSP</sub> < 7 K/W
- ESD: up to 10 kV (according to ANSI / ESDA / JEDEC<sup>®</sup> JS-001)
- Floor life: 168 h, MSL 3, according to J-STD-020E
- Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **APPLICATIONS**

- Driver and occupant monitoring
- Eye tracking
- Safety and security, CCTV

PRODUCT SUMMARY						
COMPONENT	$I_e$ (mW/sr) at $I_F$ = 1.0 A	φ (°)	λ <sub>p</sub> (nm)	$\lambda_{centroid}$ (nm)	t <sub>r</sub> (ns)	
VSMA1094601X02	460	± 60	950	945	10	

#### Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
VSMA1094601X02	Tape and reel	MOQ: 600 pcs, 600 pcs/reel	High power with lens			

Note

MOQ: minimum order quantity

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COMPLIANT

HALOGEN

FREE

GREEN (5-2008)



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## **Vishay Semiconductors**

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
Reverse voltage		V <sub>R</sub>	5	V			
Minimum forward current		I <sub>F, min.</sub>	100	mA			
Forward current		I <sub>F</sub>	1.5	А			
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	5	А			
Power dissipation		Pv	5	W			
Junction temperature		Tj	145	°C			
Ambient temperature range		T <sub>amb</sub>	-40 to +125	°C			
Storage temperature range		T <sub>stg</sub>	-40 to +125	°C			
Soldering temperature	According to Fig. 11, J-STD-020E	T <sub>sd</sub>	260	°C			
Thermal resistance junction to solder point real <sup>(1)</sup>	JESD 51	R <sub>thJSP,real</sub>	< 7	K/W			
ESD sensitivity	According to ANSI / ESDA / JEDEC JS-001	$V_{ESD}$	10	kV			

Note

<sup>(1)</sup> Thermal resistance junction to solder point real has been measured with the part mounted on an ideal heatsink and the optical output power has been deducted from the total electrical power dissipation

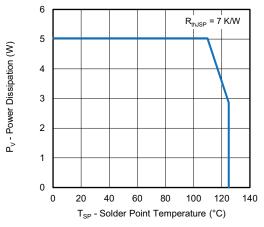


Fig. 1 - Power Dissipation Limit vs. Solder Point Temperature

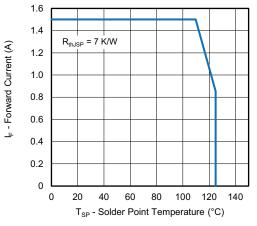


Fig. 2 - Forward Current Limit vs. Solder Point Temperature



## **Vishay Semiconductors**

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	l <sub>F</sub> = 0.35 A, t <sub>p</sub> = 10 ms	V <sub>F</sub>	2.2	2.6	3.0	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>	2.3	2.8	3.1	V
	I <sub>F</sub> = 1.5 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>	2.6	2.9	3.3	V
	$I_F = 5 \text{ A}, t_p = 100 \ \mu \text{s}$	V <sub>F</sub>	3.1	3.7	4.2	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs		-	-1.23	-	mV/K
Reverse current <sup>(1)</sup>		I <sub>R</sub>	Not designed for reverse operation $\mu$ A			
Radiant intensity	l <sub>F</sub> = 0.35 A, t <sub>p</sub> = 10 ms	l <sub>e</sub>	135	170	205	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>	370	460	550	mW/sr
	I <sub>F</sub> = 1.5 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>	550	690	830	mW/sr
	$I_F = 5 \text{ A}, t_p = 100 \ \mu \text{s}$	l <sub>e</sub>	1675	2100	2550	mW/sr
Padiant nowar	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	фе	-	1250	-	mW
Radiant power	I <sub>F</sub> = 1.5 A, t <sub>p</sub> = 100 μs	фе	-	1850	-	mW
Temperature coefficient of $\phi$	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	ΤK <sub>φ</sub>	-	-0.20	-	%/K
Angle of half intensity		φ	-	± 60	-	0
Peak wavelength	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	λρ	940	950	965	nm
Centroid wavelength	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	$\lambda_{centroid}$	-	945	-	nm
Spectral bandwidth	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	Δλ	-	35	-	nm
Temperature coefficient of $\lambda_p$	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	ΤΚ <sub>λp</sub>	-	0.31	-	nm/K
Rise time	$I_F = 1 \text{ A}, \text{ R}_L = 50 \Omega$	tr	-	10	-	ns
Fall time	$I_F = 1 \text{ A}, \text{ R}_L = 50 \Omega$	t <sub>f</sub>	-	13	-	ns

#### Note

(1) This infrared LED is designed to be operated within the specified forward current range. Continuous reverse operation must be avoided because it may damage the infrared LED.

<b>RADIANT INTENSITY BINNING</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SELECTION CODE	SYMBOL	MIN.	TYP.	MAX.	UNIT
Radiant intensity $I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$		0		370	460	550	mW/sr
	L _ 1 A + _ 100 up	1		370		430	mW/sr
	$i_{\rm F} = 1  {\rm A},  i_{\rm p} = 100  {\rm \mu s}$	2	'e	430	n/a	490	mW/sr
		3		490		550	mW/sr

#### Note

 Each reel will contain a single selection code. The label on the bag indicates the selection code. Production shipments can include multiple selection codes in multiple bags.

### BASIC CHARACTERISTICS (Tamb = 25 °C, unless otherwise specified)

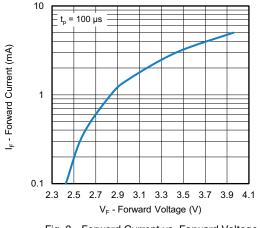


Fig. 3 - Forward Current vs. Forward Voltage

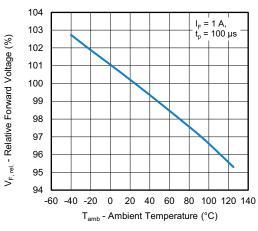


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

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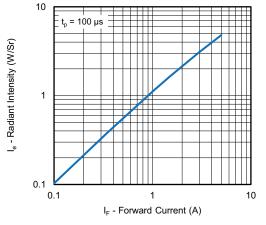


Fig. 5 - Relative Radiant Intensity vs. Forward Current

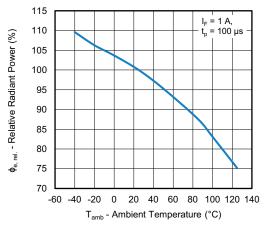


Fig. 6 - Relative Radiant Power vs. Ambient Temperature

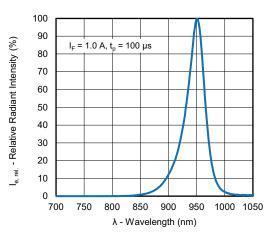


Fig. 7 - Relative Radiant Intensity vs. Wavelength

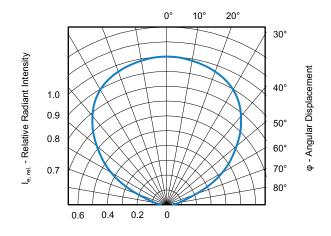


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

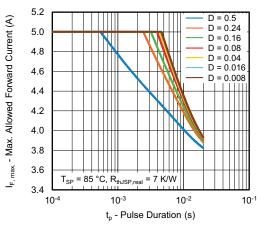


Fig. 9 - Max. Allowed Forward Current vs. Pulse Duration

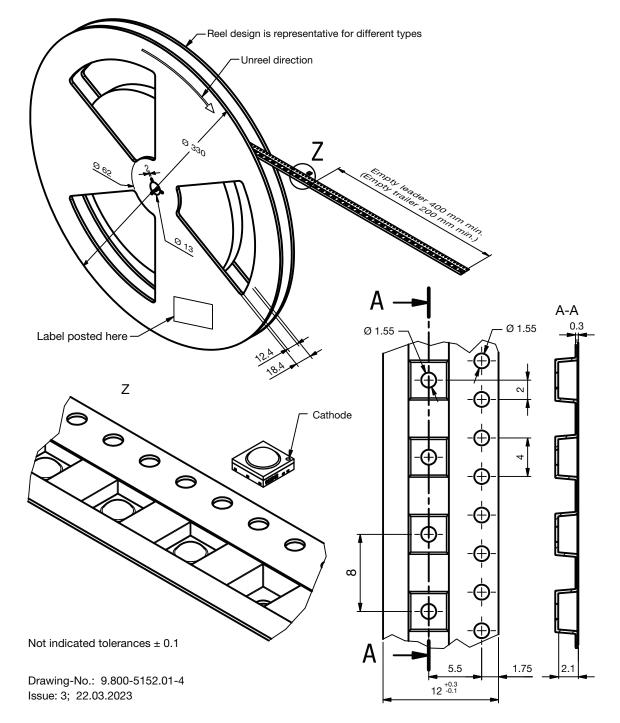
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### TAPING DIMENSIONS in millimeters



#### Notes

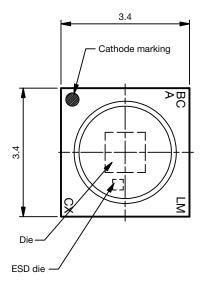
- · Empty component pockets sealed with top cover tape
- 7 inch reel 600 pieces per reel
- The maximum number of consecutive missing lamps is two
- In accordance with ANSI / EIA 481-1-A-1994 specifications

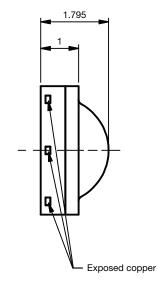


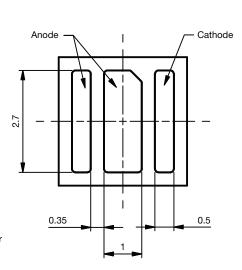
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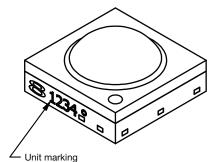
VISHAY, www.vishay.com

### **PACKAGE DIMENSIONS** in millimeters









Not indicated tolerances ± 0.1



Technical drawings according to DIN specification

Drawing-No.: 6.550-5368.01-4 Issue: 2; 22.03.2023

#### Notes

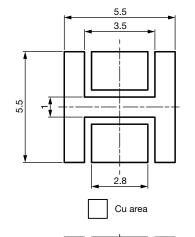
- Tolerance is ± 0.10 mm (0.004") unless otherwise noted
- Specifications are subject to change without notice

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VSMA1094601X02 **Vishay Semiconductors** 

### **RECOMMENDED FOOTPRINT**



Cathode marking

Max. 260 °C

Max. 30 s

Max. 100 s

Max. ramp down 6 °C/s

Max. 2 cycles allowed

250

300

200

245 °C

Component location on pad

Max. 120 s

Max. ramp up 3 °C/s

50

100

150

Time (s)

Fig. 10 - Lead (Pb)-free (Sn) Infrared Reflow Solder Profile

According to J-STD-020E for Surface-Mount Components

SOLDER PROFILE

255 °C

240 °C

217 °C

300

250

200

150

100

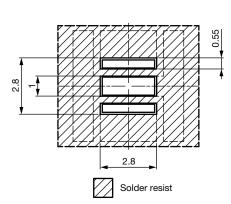
50

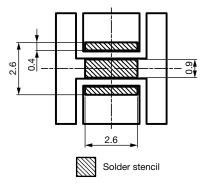
0

0

Temperature (°C)

23192





Drawing-No.: 6.550-5366.9-3 Issue: 2; 23.02.2023

### DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

### **FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

Conditions: T<sub>amb</sub> < 30 °C, RH < 60 %

Moisture sensitivity level 3, according to J-STD-020E

### DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-033D or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.





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